

3MS™ Trimethylsilane

Semiconductor Grade, Total Purity ≥ 99.995%

Product Description

3MS™ CVD Precursor is a silicon source specialty gas engineered for PECVD processes used to deposit thin film dielectrics.

Physical Characteristics

Formula	(CH ₃) ₃ SiH
Molecular Weight (g/mol)	74.19
Approx Gas Density (mg/cc)	3
Vapor Pressure at 25°C	1400 Torr

Standard Package Information

Material Number	122876
Cylinder size	X49S
Fill Weight (kg)	26
Valve Connection (DISS)	632 Manual
Cylinder Dimensions (in)	9x55

Vapor Phase Impurities

<i>Contaminants</i>		<i>Specifications</i>
CO ₂	Carbon Dioxide	≤2.0 ppmv
CO	Carbon Monoxide	≤2.0 ppmv
N ₂	Nitrogen	≤2.0 ppmv
O ₂ & Ar	Oxygen and Argon	≤2.0 ppmv
THC	Total Hydrocarbons	≤5.0 ppmv
H ₂ O	Water	≤1.0 ppmv

Liquid Phase Impurities

<i>Contaminants</i>		<i>Specifications (ppbw)</i>
	Total Chlorides	≤1.0 ppmv
Al	Aluminum	≤5.0
As	Arsenic	≤5.0
Ba	Barium	≤5.0
Bi	Bismuth	≤5.0
Ca	Calcium	≤5.0
Co	Cobalt	≤5.0
Cr	Chromium	≤5.0
Cu	Copper	≤5.0
Ga	Gallium	≤5.0
In	Indium	≤5.0
Fe	Iron	≤5.0
Pb	Lead	≤5.0
Li	Lithium	≤5.0
Mg	Magnesium	≤5.0
Mn	Manganese	≤5.0
Ni	Nickel	≤5.0
K	Potassium	≤5.0
Na	Sodium	≤5.0
Sr	Strontium	≤5.0
Th	Thorium	≤5.0
Sn	Tin	≤5.0
Ti	Titanium	≤5.0
W	Tungsten	≤5.0
U	Uranium	≤5.0
Zn	Zinc	≤5.0

For More Information

If you would like additional information or technical assistance in preparing specific formulations, write or call Air Products and Chemicals, Inc. at the following location.

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